NSN 5961-01-157-0362

Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:
Ceramic
Component Name And Quantity:
5 semiconductor device diode
Mounting Method:
Terminal
Voltage Rating In Volts Per Characteristic:
15.0 collector to emitter voltage/static/base open all semiconductor device diode and 20.0 collector to base voltage/static/emitter open all
semiconductor device diode and 5.0 emitter to base voltage, static, collector open all semiconductor device diode
Current Rating Per Characteristic:
20.00 milliamperes zero-gate-voltage source current of standard range all semiconductor device diode and 100.00 milliamperes
zero-gate-voltage source current blank all semiconductor device diode
Power Rating Per Characteristic:
750.0 milliwatts small-signal input power, common-collector preset all semiconductor
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius ambient air
Special Features:
All semiconductor device diode junction pattern arrangement: pnp
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0